

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 2, line 4 in "clean" format, as follows:

Step 1: As shown in Fig. 1A, a conductive film of a refractory (high-melting point) metal such as chromium is formed on the glass substrate 51. The conductive film is etched in a predetermined pattern to form a gate electrode 52. Next, a gate insulating film 53, which is a laminated structure of a silicon dioxide and a silicon nitride, is formed covering the gate electrodes 52, and then a semiconductor layer 54 of a silicon, and an ion stopper 55 of a silicon dioxide are sequentially formed.

IN THE CLAIMS:

Please amend claim 3 in "clean" format, as follows:

3. (Amended) A method for manufacturing a bottom gate-type thin-film transistor on a transparent insulating substrate, comprising the steps of:

- forming a gate electrode on a transparent substrate;
- forming a gate insulating film on said gate electrode;
- forming a semiconductor layer on said gate insulating film;
- forming a mask on said semiconductor layer corresponding to said gate electrode;
- doping impurities selectively into said semiconductor layer, using said mask; and
- forming an interlayer insulating film directly on said semiconductor layer, after removal of said mask.

Please add claims 6-10, as follows:

6. (Newly Added) A method defined in Claim 3, wherein the mask of at least some of a plurality of thin film transistors is shorter than the gate electrode in a channel length direction, and a region doped with impurities in the semiconductor layer thereof overlaps the gate electrode.